



PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at



Datasheet



Resources

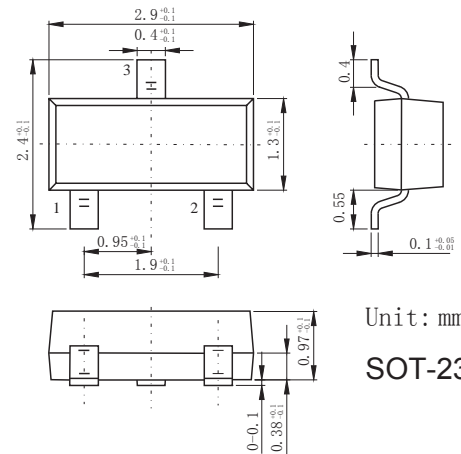
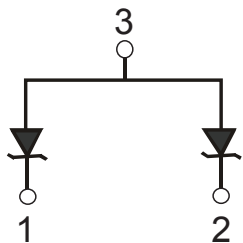


Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

■ Features

- 300 Watts Peak Pulse Power ($t_p = 8/20\mu s$)
- Transient protection for data & power lines to
 - IEC 61000-4-2 (ESD) $\pm 15kV$ (air), $\pm 8kV$ (contact)
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 12A (8/20 μs)
- Working Voltages: 5V, 12V, 15V, 24 and 36V
- Low clamping voltage


■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Peak Pulse Power ($t_p = 8/20\mu s$)	P _{PK}	300	W
Thermal Resistance Junction to Ambient *3	R _{θJA}	556	°C/W
Lead Soldering Temperature	T _L	260	°C
Junction Temperature	T _J	125	
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

SM05

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	6			V
Reverse Stand-Off Voltage	V _{RWM}				5	
Clamping Voltage	V _C	I _{PP} = 1 A, t _P =8/20us			9.8	
Reverse Leakage Current	I _R	V _R =5 V			20	uA
Peak Pulse Current	I _{PP}	t _P =8/20us			17	A
Junction Capacitance	C _J	Pin 1 to 2 ,V _R = 0V,f=1MHz			350	pF
		Pin 1 to 2 and Pin 2 to 3 ,V _R = 0V,f=1MHz			400	

■ Electrical Characteristics Ta = 25°C
SM12

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	13.3			V
Reverse Stand-Off Voltage	V _{RWM}				12	
Clamping Voltage	V _C	I _{PP} = 1 A, t _P =8/20us			19	
Reverse Leakage Current	I _R	V _R =12 V			1	uA
Peak Pulse Current	I _{PP}	t _P =8/20us			12	A
Junction Capacitance	C _J	Pin 1 to 2 ,V _R = 0V,f=1MHz			120	pF
		Pin 1 to 2 and Pin 2 to 3 ,V _R = 0V,f=1MHz			150	

SM15

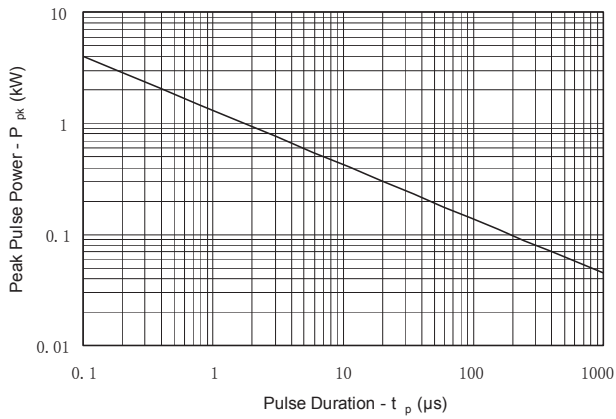
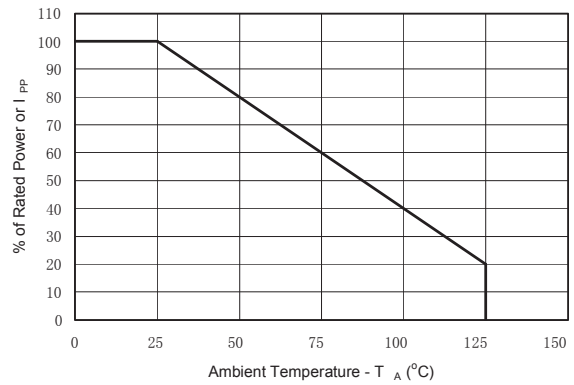
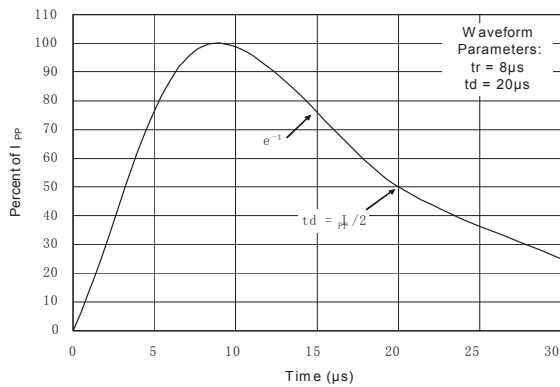
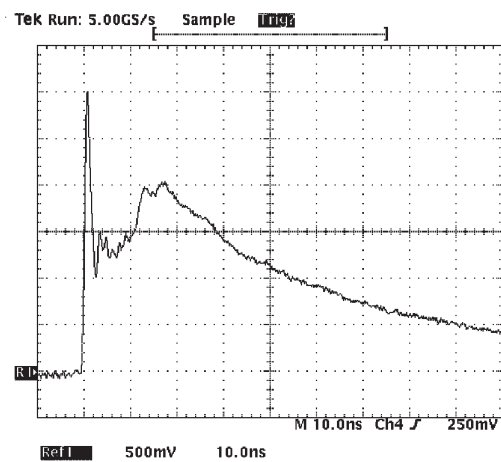
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	16.7			V
Reverse Stand-Off Voltage	V _{RWM}				15	
Clamping Voltage	V _C	I _{PP} = 1 A, t _P =8/20us			24	
Reverse Leakage Current	I _R	V _R =15 V			1	uA
Peak Pulse Current	I _{PP}	t _P =8/20us			10	A
Junction Capacitance	C _J	Pin 1 to 2 ,V _R = 0V,f=1MHz			75	pF
		Pin 1 to 2 and Pin 2 to 3 ,V _R = 0V,f=1MHz			100	

SM24

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	26.7			V
Reverse Stand-Off Voltage	V _{RWM}				24	
Clamping Voltage	V _C	I _{PP} = 1 A, t _P =8/20us			43	
Reverse Leakage Current	I _R	V _R =24 V			1	uA
Peak Pulse Current	I _{PP}	t _P =8/20us			5	A
Junction Capacitance	C _J	Pin 1 to 2 ,V _R = 0V,f=1MHz			50	pF
		Pin 1 to 2 and Pin 2 to 3 ,V _R = 0V,f=1MHz			60	

SM36

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	40			V
Reverse Stand-Off Voltage	V _{RWM}				36	
Clamping Voltage	V _C	I _{PP} = 1 A, t _P =8/20us			60	
Reverse Leakage Current	I _R	V _R =36 V			1	uA
Peak Pulse Current	I _{PP}	t _P =8/20us			4	A
Junction Capacitance	C _J	Pin 1 to 2 ,V _R = 0V,f=1MHz			40	pF
		Pin 1 to 2 and Pin 2 to 3 ,V _R = 0V,f=1MHz			45	

Typical Characteristics
Non-Repetitive Peak Pulse Power vs. Pulse Time

Power Derating Curve

Pulse Waveform

ESD Pulse Waveform (Per IEC 61000-4-2)

IEC 61000-4-2 Discharge Parameters

Level	First Peak Current (A)	Peak Current at 30 ns (A)	Peak Current at 60 ns (A)	Test Voltage (Contact Discharge) (kV)	Test Voltage (Air Discharge) (kV)
1	7.5	4	8	2	2
2	15	8	4	4	4
3	22.5	12	6	6	8
4	30	16	8	8	15

Attention

1, Any and all JGSEMI products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical or material damage. Consult with your JGSEMI representative nearest you before using any JGSEMI products described or contained herein in such applications.

2, JGSEMI assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all JGSEMI products described or contained herein.

3, Specifications of any and all JGSEMI products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, In the event that any or all JGSEMI products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

5, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of JGSEMI Semiconductor CO., LTD.

6, Any and all information described or contained herein are subject to change without notice due to product technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the JGSEMI product that you intend to use.